PTO/SB/08A (04-03)
Approved for use 04-30-2003. OMB 0651-0031

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet	1	Of	8

COMPLETE IF KNOWN	
Application Number	10/026,019
Filing Date	December 27, 2001
First Named Inv ntor	Ralph Johnson
Art Unit	2828
Examiner Name	Tuan M Nguyen
Attorney Docket Number	V637-02674 US

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No[1]	Document Number: Number	Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear
DV		US 4445218		04-24-1984	Coldren	
		US 4608697		08-26-1986	Coldren	
		US 4622672		11-11-1986	Coldren et al.	
		US 4829347		05-09-1989	Cheng et al.	
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		US 5719894	A	02-17-1998	Jewell et al.	

Examiner Signature	MV	Date Considered	08/04/04

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Sheet	2	Of	8

COMPLETE IF KNOWN	
Application Number	10/026,019
Filing Date	December 27, 2001
First Named Inventor	Ralph Johnson
Group Art Unit	2828
Examiner Name	Tuan M Nguyen
Attorney Docket Number	V637-02674 US

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Sheet	3	Of	8

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Filing Date	December 27, 2001
First Named Inventor	Ralph Johnson
Group Art Unit	2828
Examiner Name	Tuan M Nguyen
Attorney Docket Number	V637-02674 US

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Sheet	4	Of	8

COMPLETE IF KNOWN	
Application Number	10/026,019
Filing Dat	December 27, 2001
First Named Inventor	Ralph Johnson
Group Art Unit	2828
Examiner Name	Tuan M Nguyen
Attorney Docket Number	V637-02674 US

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No[1]	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear	T[6]
		Country Code[3]	Number[4]	Kind Code[5] (if known)				
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Sheet	5	Of	8

COMPLETE IF KNOWN	
Application Number	10/026,019
Filing Date	December 27, 2001
First Named Inventor	Ralph Johnson
Group Art Unit	2828
Examiner Name	Tuan M Nguyen
Attorney Docket Number	V637-02674 US

DW		WO	01/018919	A1	03-15-2001	The Regents of the University of California		
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T[2]
DW		ALMUNEAU, G., et al., "Accurate control of Sb composition in AlGaAsSb alloys on InP substrates by molecular beam epitaxy", article, Journal of Crystal Growth, Vol 208, 05-06-1999, pgs 113-6.	
		ALMUNEAU, G., et al., "Improved electrical and thermal properties of InP-AlGaAsSb Bragg mirrors for long-wavelength vertical-cavity lasers", article, IEEE Photonics Technology Letters, Vo. 12, No 10, Oct 2000, pgs 1322-4,	
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Sheet	6	Of	8

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Application Number	10/026,019
Filing Date	December 27, 2001
First Named Inventor	Ralph Johnson
Group Art Unit	2828
Examiner Name	Tuan M Nguyen
Attorney Docket Number	V637-02674 US

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Attorney Docket Number	V637-02674 US

MV		KIM, J., et al., "Epitaxially-stacked multiple-active-region 1.55 μm lasers for increased differential efficiency", article, Applied Physics Letters, Vol 74, No 22, 05-31-1999, pgs 3251-3.	
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Examiner Signature		Date Considered	02/04/04

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Sheet	8	Of	8

COMPLETE IF KNOWN	
Application Number	10/026,019
Filing Dat	December 27, 2001
First Named Inventor	Ralph Johnson
Group Art Unit	2828
Examiner Name	Tuan M Nguyen
Attorney Docket Number	V637-02674 US

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Sheet	2	Of	2

COMPLETE IF KNOWN	
Application Number	10/026,019
Filing Date	December 20, 2001
First Named Inventor	Ralph Johnson
Group Art Unit	2828
Examiner Name	Tuan M Nguyen
Attorney Docket Number	V637-02674 US

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T[2]
DW		ANAN, T., et al., "Continuous-wave operation of 1.30 um GaAsSb/GaAs VCSELs", article, Electronics Letters, Vol 37, N0 9, 04-26-2001, pgs 566-7.	
DW		YANG, X., et.al., "High-temperature characteristics of 1.3 um InGaAsN:Sb/GaAs multiple-quantum-well lasers grown by molecular-beam epitaxy", article, Applied Physics Letters, Vol 76, No 7, 02-14-2000, pgs 795-7.	

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First Named Inventor	Ralph Johnson
Art Unit	2828
Examiner Name	Tuan M Nguyen
Attorney Docket Number	V637-002674 US

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DW		EP	0 975 073	A1	01-26-2000	NEC Corporation		

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DW		LIVSHITS, D., et al., "8W continuous wave operation of InGaAsN lasers of 1.3 μm", article, Electronics Letters, Vol 36, No 16, 08-03-2000, pgs 1381-2.International Search Report, dated 03-27-2003, relative to PCT application No. PCT/US 02/39414, the foreign equivalent to the instant U.S. application 10/026,055.	

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DV		WO	01/33677	A2	05-10-2001	Arizona Board of Regents		
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